

1. Material Substrate GaAs (N Type)
Epitaxial Layer AlGaAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

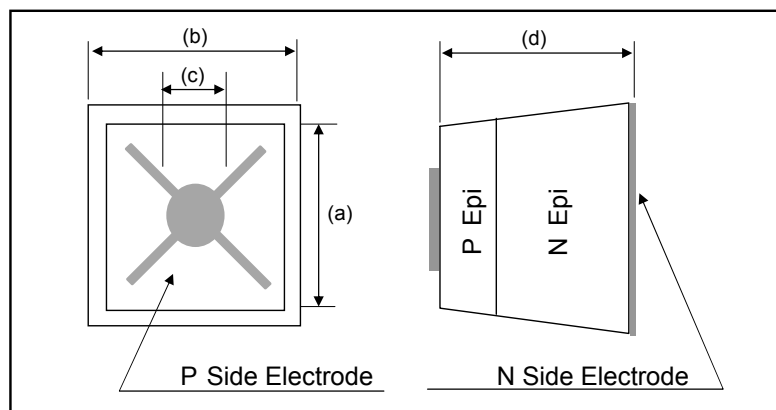
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			2.0	V	IF=50mA
Reverse Current	V_R	8			V	IR=10uA
Power	P_O	9			mW	IF=50mA
Wavelength	λ_P		770		nm	IF=50mA
	$\Delta\lambda$		30		nm	IF=50mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	-----	15.0mil x 15.0mil
(b) Bottom Area	-----	16.0mil x 16.0mil
(c) Bonding Pad	-----	130um
(d) Chip Thickness	-----	7.8mil



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